

AD2500-9 TO5i

Avalanche Photodiode, NIR enhanced

Special characteristics:

high gain at low bias voltage
fast rise time
2500 μm diameter active area
low capacitance



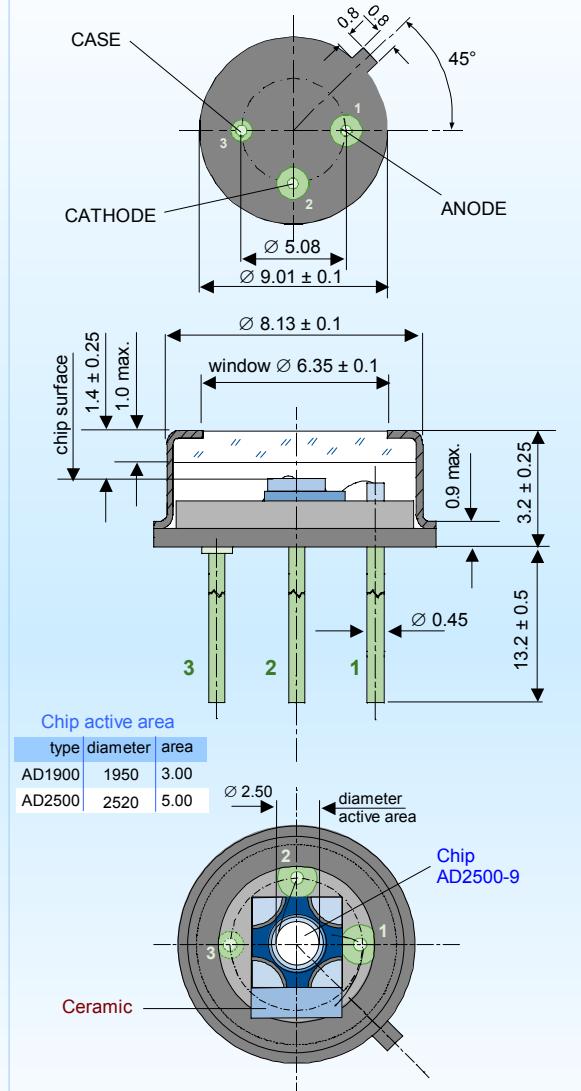
| Parameters: | AD2500-9 TO5i |
|---|---|
| Active Area | 5.0 mm ² Ø 2520 μm |
| Dark Current ¹⁾ (M = 100) | max. 30 nA typ. 20.0 nA |
| Total Capacitance ¹⁾ (M = 100) | typ. 12 pF |
| Breakdown Voltage U _{BR} (at I _D = 2 μA) | 120 ... 300 V typ. > 200 V |
| Temperature Coefficient of U _{BR} | typ. 1.55 V/K |
| Spectral Responsivity ¹⁾ (at 905 nm, M = 100) | min. 55 A/W typ. 60 A/W |
| Cut-off Frequency (-3dB) | typ. 0.2 GHz |
| Rise Time at 905 nm, 50 Ω | typ. 1.6 ns |
| Max. Gain | > 200 |
| "Excess Noise" factor (M = 100) | typ. 2.5 |
| "Excess Noise" index (M = 100) | typ. 0.2 |
| N.E.P. (M = 100, 905 nm) | typ. 3* 10 ⁻¹³ W/Hz ^{1/2} |
| Operating Temperature | -20 ... +70 °C |
| Storage Temperature | -60 ... +100 °C |

1) measurement conditions:

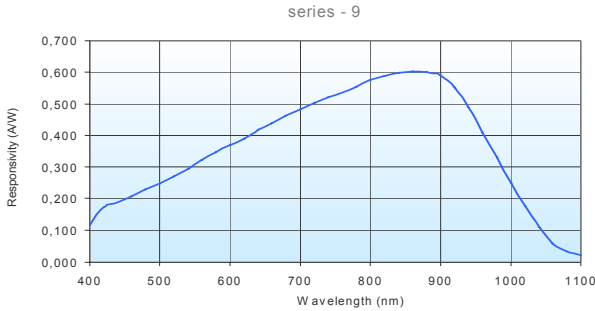
Setup of photo current 10 nA at M = 1 and irradiation by a IRED
(880 nm, 80 nm bandwidth).

Increase the photo current up to 1 μA , (M = 100) by internal multiplication
due to an increasing bias voltage

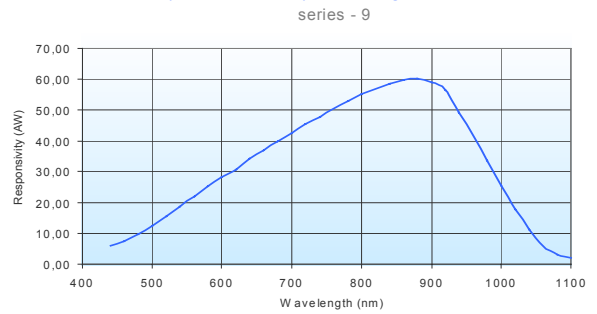
Package 3a (TO5i):



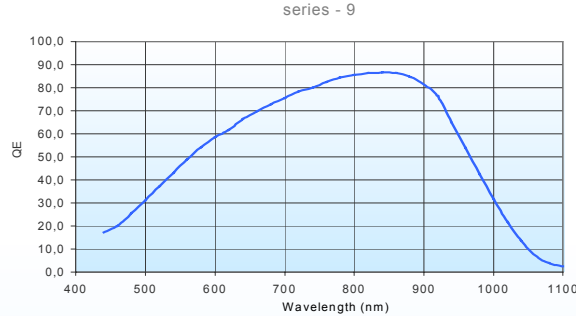
Spectral Responsivity at M=1



Spectral Responsivity at M=100

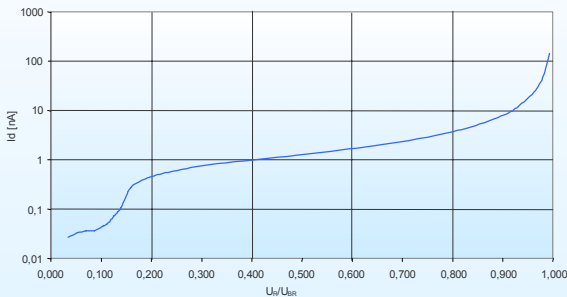


Quantum Efficiency for M = 100



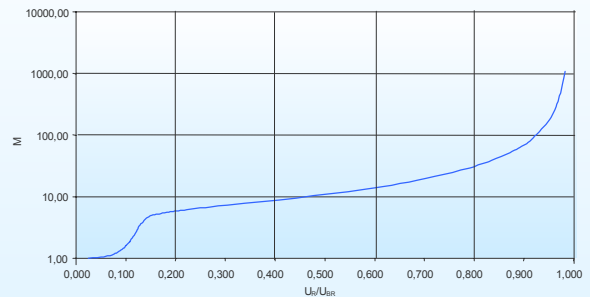
$$I_D = f(U_R/U_{BR})$$

AD2500-9



$$M = (U_R/U_{BR})$$

AD2500-9



Maximum Ratings:

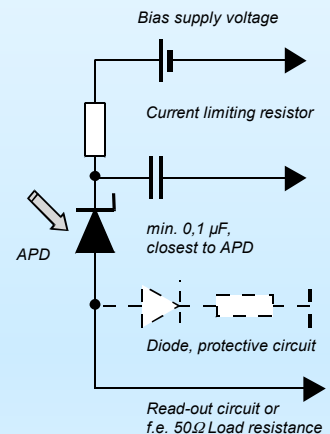
- max. electrical power dissipation 100 mW at 22°C
- max. optical peak value, once 200 mW for 1 s
- max. continuous optical operation $I_{ph} (DC) \leq 250 \mu A$
 $\leq 1 \text{ mA}$ for signal 50 μs "on" / 1 ms "off"
- $(P_{electr.} = P_{opt.} * S_{abs} * M * U_R)$

Application Hints:

- Current should be limited by a protecting resistor or current limiting - IC inside the power supply.
- Use of low noise read-out - IC.
- For high gain applications bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

Handling Precautions:

- Soldering temperature 260 °C for max. 10 s. The device must be protected against solder flux vapour!
- min. Pin - length 2 mm
- ESD - protection Standard precautionary measures are sufficient.
- Storage Store devices in conductive foam.
- Avoid skin contact with window!
- Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.



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